

RF MOS FIELD EFFECT TRANSISTOR

DESCRIPTION:

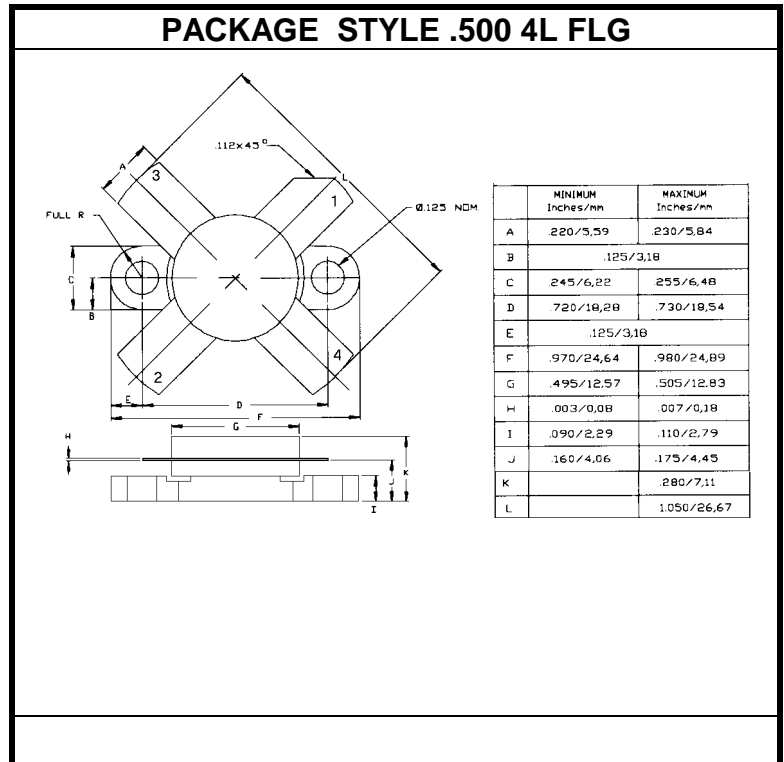
The **SRF4245** is Designed for class AB HF/VHF Applications up to 200 MHz

FEATURES:

- $P_G = 8$ dB at 150 MHz
- **Omnigold™** Metallization System

MAXIMUM RATINGS

I_D	13.9 A
$V_{(BR)DS}$	125 V
V_{DGR}	125 V
V_{GS}	± 30 V
P_{DISS}	215 W @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+150^\circ C$
θ_{JC}	0.70 (Typ) $^\circ C/W$


CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
$V_{(BR)DSS}$	$V_{GS} = 0$ V	$I_D = 100$ mA		125			V
I_{DSS}	$V_{DS} = 50$ V	$V_{GS} = 0$ V				5	mA
I_{GSS}	$V_{GS} = 20$ V	$V_{DS} = 0$ V				1	μA
$V_{FEDS(on)}$	$V_{GS} = 10$ V	$I_D = 10$ A				5	V
G_{FS}	$V_{DS} = 10$ V	$I_D = 5.0$ A		4			mhos
C_{ISS}	$V_{DS} = 50$ V	$V_{GS} = 0$ V	$F = 1.0$ MHz			500	pF
C_{OSS}						250	
C_{RSS}						50	
P_{OUT}	$V_{DS} = 50$ V	$I_{DQ} = 250$ mA	$F = 150$ MHz	150			W
P_G				8			dB

